# **ON5088**

# NPN wideband silicon germanium RF transistor

Rev. 3 — 12 December 2012

Product data sheet

## 1. Product profile

### 1.1 General description

NPN silicon germanium microwave transistor for high speed, low noise applications in a plastic, 4-pin dual-emitter SOT343F package.

#### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

#### 1.2 Features and benefits

- Low noise high gain microwave transistor
- High maximum stable gain 27 dB at 1.8 GHz
- 110 GHz f<sub>T</sub> silicon germanium technology

### 1.3 Applications

- 2nd and 3rd LNA stage in DBS LNBs
- Satellite radio
- Low noise amplifiers for microwave communications systems
- WLAN and WiMAX applications
- Analog/digital cordless applications

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	М	in	Тур	Max	Unit
$V_{CB}$	collector-base voltage	open emitter	-		-	10	V
V <sub>CE</sub>	collector-emitter voltage	open base	-		-	3.0	V
		shorted base	-		-	10	V
$V_{EB}$	emitter-base voltage	open collector	-		-	1.0	V
I <sub>C</sub>	collector current		-		25	40	mA
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> ≤ 90 °C	<u>[1]</u> -		-	136	mW
h <sub>FE</sub>	DC current gain	$I_C = 10 \text{ mA}; V_{CE} = 2 \text{ V};$ $T_j = 25 \text{ °C}$	16	60	280	400	
C <sub>CBS</sub>	collector-base capacitance	V <sub>CB</sub> = 2 V; f = 1 MHz	-		70	-	fF



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Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>T</sub>	transition frequency	$I_C$ = 25 mA; $V_{CE}$ = 2 V; f = 2 GHz; $T_{amb}$ = 25 °C	-	55	-	GHz
$G_{p(\text{max})}$	maximum power gain	$I_C$ = 25 mA; $V_{CE}$ = 2 V; f = 12 GHz; $T_{amb}$ = 25 °C	[2] -	13	-	dB
NF	noise figure	$I_C$ = 5 mA; $V_{CE}$ = 2 V; $f$ = 12 GHz; $\Gamma_S$ = $\Gamma_{opt}$ ; $T_{amb}$ = 25 °C	-	1.1	-	dB

<sup>[1]</sup>  $T_{sp}$  is the temperature at the solder point of the emitter lead.

## 2. Pinning information

Table 2. Discrete pinning

	p		
Pin	Description	Simplified outline	Graphic symbol
1	emitter		
2	base	3 4	4 
3	emitter		2 —
4	collector		.)
		2 1	1, 3 mbb159
		2 1	MDD159

## 3. Ordering information

Table 3. Ordering information

Type number Packag			
	Name	Description	Version
ON5088	-	plastic surface-mounted flat pack package; reverse pinning; 4 leads	SOT343F

## 4. Marking

Table 4. Marking

Type number	Marking	Description		
ON5088	*6N	* = p : made in Hong Kong		
		* = t : made in Malaysia		
		* = W : made in China		

<sup>[2]</sup>  $G_{p(max)}$  is the maximum power gain, if K > 1. If K < 1 then  $G_{p(max)}$  = Maximum Stable Gain (MSG).

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## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CB}$	collector-base voltage	open emitter	-	10	V
$V_{CE}$	collector-emitter voltage	open base	-	3.0	V
		shorted base	-	10	V
$V_{EB}$	emitter-base voltage	open collector	-	1.0	V
I <sub>C</sub>	collector current		-	40	mA
P <sub>tot</sub>	total power dissipation	$T_{sp} \le 90  ^{\circ}C$	<u>[1]</u> _	136	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		-	150	°C

<sup>[1]</sup>  $T_{sp}$  is the temperature at the solder point of the emitter lead.

### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		440	K/W

### 7. Characteristics

Table 7. Characteristics

 $T_j = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 2.5 \mu A; I_E = 0 \text{ mA}$	10	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = 1 \text{ mA}$ ; $I_B = 0 \text{ mA}$	3.0	-	-	V
I <sub>C</sub>	collector current		-	25	40	mΑ
I <sub>CBO</sub>	collector-base cut-off current	$I_E = 0 \text{ mA}; V_{CB} = 4.5 \text{ V}$	-	-	100	nΑ
h <sub>FE</sub>	DC current gain	$I_C = 10 \text{ mA}; V_{CE} = 2 \text{ V}$	160	280	400	
C <sub>CES</sub>	collector-emitter capacitance	V <sub>CB</sub> = 2 V; f = 1 MHz	-	268	-	fF
C <sub>EBS</sub>	emitter-base capacitance	V <sub>EB</sub> = 0.5 V; f = 1 MHz	-	400	-	fF
C <sub>CBS</sub>	collector-base capacitance	$V_{CB} = 2 \text{ V}; f = 1 \text{ MHz}$	-	70	-	fF
f <sub>T</sub>	transition frequency	$I_C$ = 25 mA; $V_{CE}$ = 2 V; f = 2 GHz; $T_{amb}$ = 25 °C	-	55	-	GHz
G <sub>p(max)</sub>	maximum power gain	$I_C$ = 25 mA; $V_{CE}$ = 2 V; $T_{amb}$ = 25 °C	[1]			
		f = 1.8 GHz	-	27	-	dB
		f = 12 GHz	-	13	-	dB
$ s_{21} ^2$	insertion power gain	$I_C$ = 25 mA; $V_{CE}$ = 2 V; $T_{amb}$ = 25 °C				
		f = 1.8 GHz	-	25.4	-	dB
		f = 12 GHz	-	9.3	-	dB

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**Table 7.** Characteristics ...continued  $T_i = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
NF noise figure		$I_C$ = 5 mA; $V_{CE}$ = 2 V; $\Gamma_S$ = $\Gamma_{opt}$ ; $T_{amb}$ = 25 °C				
	f = 1.8 GHz	-	0.43	-	dB	
	f = 12 GHz	-	1.1	-	dB	
G <sub>ass</sub> associated gain		$I_C$ = 5 mA; $V_{CE}$ = 2 V; $\Gamma_S$ = $\Gamma_{opt}$ ; $T_{amb}$ = 25 °C				
	f = 1.8 GHz	-	22	-	dB	
		f = 12 GHz	-	10	-	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	$\rm I_C$ = 25 mA; $\rm V_{CE}$ = 2 V; $\rm Z_S$ = $\rm Z_L$ = 50 $\rm \Omega;$ $\rm T_{amb}$ = 25 °C; f = 1.8 GHz	-	9	-	dBm
IP3	third-order intercept point	$I_C$ = 25 mA; $V_{CE}$ = 2 V; $Z_S$ = $Z_L$ = 50 $\Omega$ ; $T_{amb}$ = 25 °C; $f_2$ = $f_1$ + 1 MHz; $f_1$ = 1.8 GHz	-	17	-	dBm

<sup>[1]</sup>  $G_{p(max)}$  is the maximum power gain, if K > 1. If K < 1 then  $G_{p(max)} = MSG$ .

### NPN wideband silicon germanium RF transistor

## 8. Package outline

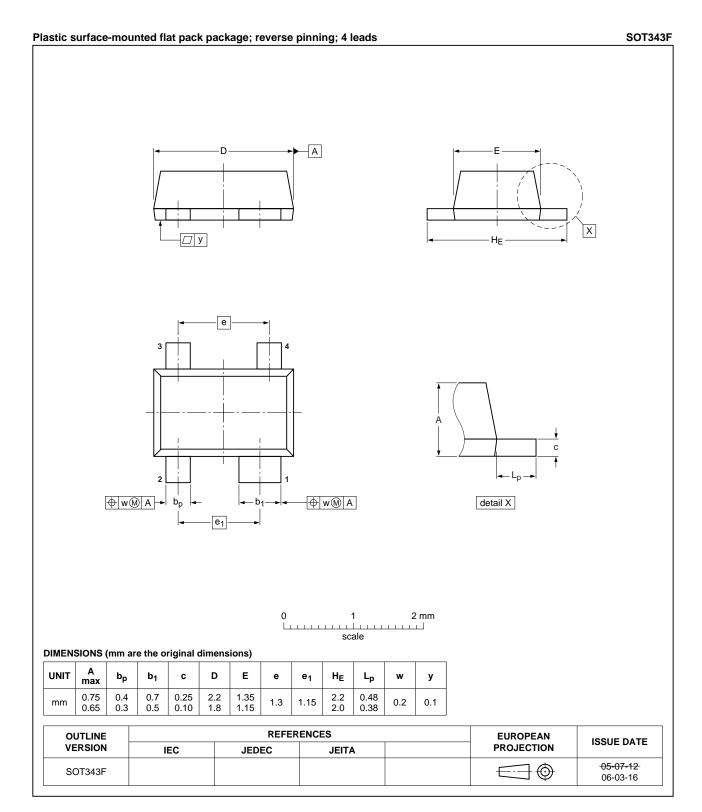


Fig 1. Package outline SOT343F

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## NPN wideband silicon germanium RF transistor

## 9. Abbreviations

Table 8. Abbreviations

Acronym	Description
DBS	Direct Broadcast Satellite
DC	Direct Current
DRO	Dielectric Resonator Oscillator
LNA	Low Noise Amplifier
LNB	Low Noise Block
NPN	Negative-Positive-Negative
RF	Radio Frequency
WLAN	Wireless Local Area Network
WiMAX	Worldwide Interoperability for Microwave Access

# 10. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
ON5088 v.3	20121212	Product data sheet	-	ON5088 v.2
Modifications:	• Table 1 on p	age 1: some changes have be	en made.	
	<ul> <li>Table 5 on p</li> </ul>	age 3: some changes have be	en made.	
	<ul><li>Table 7 on p</li></ul>	age 3: The minimum value for	V <sub>(BR)CEO</sub> has been o	changed.
ON5088 v.2	20111222	Product data sheet	-	ON5088 v.1
ON5088 v.1	20100422	Product data sheet	-	-

#### NPN wideband silicon germanium RF transistor

## 11. Legal information

#### 11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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